AUTOMOTIVE

RoHS

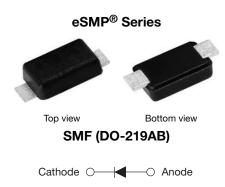
COMPLIANT

HALOGEN FREE



### Vishay Semiconductors

# Hyperfast Rectifier, 1 A FRED Pt®



#### **LINKS TO ADDITIONAL RESOURCES**



PRIMARY CHARACTERISTICS				
I <sub>F(AV)</sub>	1 A			
V <sub>R</sub>	200 V			
V <sub>F</sub> at I <sub>F</sub> (typ. 125 °C)	0.74 V			
t <sub>rr</sub>	25 ns			
T <sub>J</sub> max.	175 °C			
Package	SMF (DO-219AB)			
Circuit configuration	Single			

#### **FEATURES**

- Hyperfast recovery time, reduced Q<sub>rr</sub>, and soft recovery
- 175 °C maximum operating junction temperature
- Specified for output and snubber operation
- Low forward voltage drop
- Low leakage current
- Meets MSL level 1, per J-STD-020, LF maximum peak of 260 °C
- Wave and reflow solderable
- Compatible to SOD-123W package case outline
- AEC-Q101 qualified, meets JESD 201 class 2 whisker test
- Material categorization: for definitions of compliance please see <a href="https://www.vishay.com/doc?99912">www.vishay.com/doc?99912</a>

### **DESCRIPTION / APPLICATIONS**

State of the art hyperfast recovery rectifiers designed with optimized performance of forward voltage drop and hyperfast recovery.

The planar structure and the platinum doped life time control guarantee the best overall performance, ruggedness, and reliability characteristics.

These devices are intended for use in snubber boost, lighting, piezo-injection, as high frequency rectifiers, and freewheeling diodes.

Their extremely optimized stored charge and low recovery current minimize the switching losses and reduce power dissipation in the switching element.

### **MECHANICAL DATA**

Case: SMF (DO-219AB)

Molding compound meets UL 94 V-0 flammability rating

Halogen-free, RoHS-compliant

Terminals: matte tin plated leads, solderable per

J-STD-002

Polarity: color band denotes cathode end

ABSOLUTE MAXIMUM RATINGS				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Peak repetitive reverse voltage	$V_{RRM}$		200	V
Average rectified forward current	I <sub>F(AV)</sub>	T <sub>C</sub> = 160 °C <sup>(1)</sup>	1	^
Non-repetitive peak surge current	I <sub>FSM</sub>	T <sub>J</sub> = 25 °C	35	Α
Operating junction and storage temperature range	T <sub>J</sub> , T <sub>Stg</sub>		-65 to +175	°C

### Note

(1) Device on PCB with 8 mm x 16 mm soldering lands



<b>ELECTRICAL SPECIFICATIONS</b> (T <sub>J</sub> = 25 °C unless otherwise specified)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Breakdown voltage, blocking voltage	$V_{BR}, V_{R}$	I <sub>R</sub> = 100 μA	200	-	-	
Forward voltage	V <sub>F</sub>	I <sub>F</sub> = 1 A	-	0.87	0.93	V
Forward voltage		I <sub>F</sub> = 1 A, T <sub>J</sub> = 125 °C	-	0.74	0.8	
Reverse leakage current		V <sub>R</sub> = V <sub>R</sub> rated	-	-	2	
Reverse leakage current	$T_J = 125$ °C, $V_R = V_R$ rated	-	0.5	8	μA	
Junction capacitance	C <sub>T</sub>	$V_{R} = 200 \text{ V}$	-	5	-	pF

<b>DYNAMIC RECOVERY CHARACTERISTICS</b> (T <sub>J</sub> = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNITS
		$I_F = 1 A, dI_F/dt = 50 A$	/μs, V <sub>R</sub> = 30 V	-	24	-	
Reverse recovery time	t <sub>rr</sub>	$I_F = 0.5 \text{ A}, I_R = 1 \text{ A}, I_{rr} = 0.25 \text{ A}$		-	-	25	200
neverse recovery time		T <sub>J</sub> = 25 °C	I <sub>F</sub> = 1 A dI <sub>F</sub> /dt = 200 A/μs V <sub>R</sub> = 160 V	-	16	-	ns
		T <sub>J</sub> = 125 °C		-	23	-	
Dools recovery overent	Peak recovery current I <sub>RRM</sub>	T <sub>J</sub> = 25 °C		-	1.6	-	А
Feak recovery current		T <sub>J</sub> = 125 °C		-	2.5	-	
Deverge vegeven share	0	T <sub>J</sub> = 25 °C		-	13	-	nC
Reverse recovery charge	$Q_{rr}$	T <sub>J</sub> = 125 °C		-	30	-	IIC

THERMAL - MECHANICAL SPECIFICATIONS						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Maximum junction and storage temperature range	T <sub>J</sub> , T <sub>Stg</sub>		-65	-	+175	°C
Thermal resistance, junction to mount	R <sub>thJM</sub>	Device mounted on PCB with 8 mm x 16 mm soldering lands	-	-	17	°C/W
Thermal resistance, junction to ambient	R <sub>thJA</sub>	Device mounted on PCB with 2 mm x 3.5 mm soldering lands	-	-	140	°C/W
Approximate weight				0.015		g
Approximate weight				0.0005		oz.
Marking device		Case style SMF (DO-219AB)		MI	DH	•

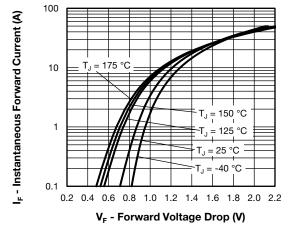


Fig. 1 - Typical Forward Voltage Drop Characteristics

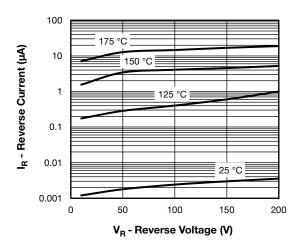


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

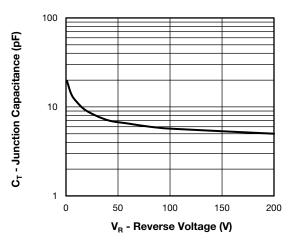


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

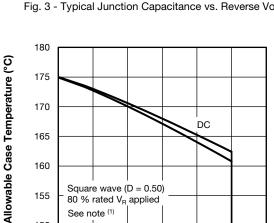


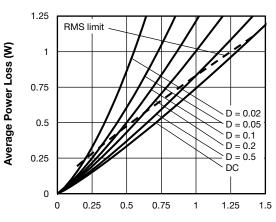
Fig. 4 - Maximum Allowable Case Temperature vs. Average Forward Current

0.6

I<sub>F(AV)</sub> - Average Forward Current (A)

0.8

1.2



I<sub>F(AV)</sub> - Average Forward Current (A)

Fig. 5 - Forward Power Loss Characteristics

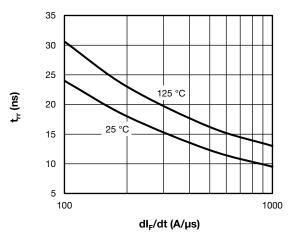


Fig. 6 - Typical Reverse Recovery Time vs. dl<sub>F</sub>/dt

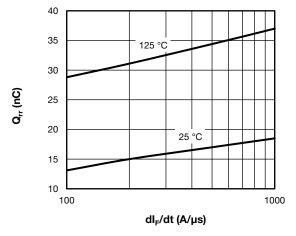


Fig. 7 - Typical Stored Charge vs. dl<sub>F</sub>/dt

#### Note

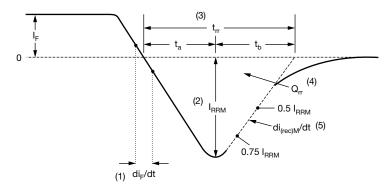
150

0

0.2

0.4

 $^{(1)}$  Formula used:  $T_{C} = T_{J}$  - (Pd + Pd\_{REV}) x  $R_{thJC};$ Pd = Forward power loss =  $I_{F(AV)}$  x  $V_{FM}$  at  $(I_{F(AV)}/D)$  (see fig. 5);  $Pd_{REV}$  = Inverse power loss =  $V_{R1} \times I_R (1 - D)$ ;  $I_R$  at  $V_{R1}$  = rated  $V_R$ 

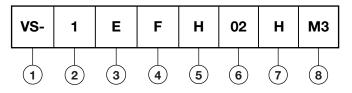


- (1) di<sub>F</sub>/dt rate of change of current through zero crossing
- (4)  $Q_{rr}$  area under curve defined by  $t_{rr}$  and  $I_{RRM}$
- (2) I<sub>RRM</sub> peak reverse recovery current
- $Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$
- (3) t<sub>rr</sub> reverse recovery time measured from zero crossing point of negative going I<sub>F</sub> to point where a line passing through 0.75 I<sub>RBM</sub> and 0.50 I<sub>RBM</sub> extrapolated to zero current.
- (5) di<sub>(rec)M</sub>/dt peak rate of change of current during t<sub>b</sub> portion of t<sub>rr</sub>

Fig. 8 - Reverse Recovery Waveform and Definitions

### **ORDERING INFORMATION TABLE**

### **Device code**



- 1 Vishay Semiconductors product
- 2 Current rating (1 = 1 A)
- 3 Circuit configuration:

E = single diode

4 - F = SMF package

5 - Process type,

H = hyperfast recovery

Voltage code (02 = 200 V)

7 - H = AEC-Q101 qualified

M3 = halogen-free, RoHS-compliant, and terminations lead (Pb)-free

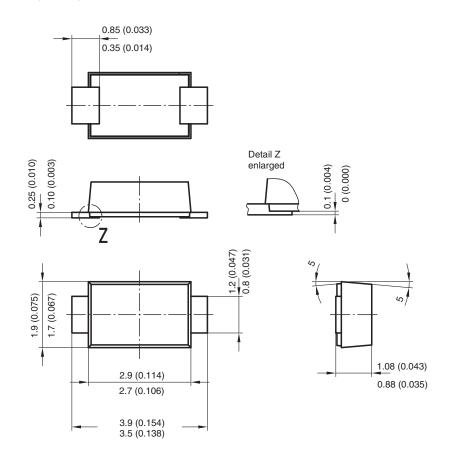
ORDERING INFORMATION (Example)						
PREFERRED P/N	QUANTITY PER REEL	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION			
VS-1EFH02HM3/I	10 000	10 000	13"diameter plastic tape and reel			

LINKS TO RELATED DOCUMENTS				
Dimensions <u>www.vishay.com/doc?95572</u>				
Part marking information	www.vishay.com/doc?95618			
Packaging information	www.vishay.com/doc?95577			
SPICE model	www.vishay.com/doc?96012			

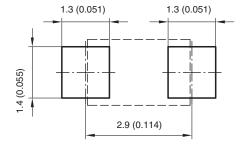


# **SMF (DO-219AB)**

### **DIMENSIONS** in millimeters (inches)



#### Foot print recommendation:



Created - Date: 15. February 2005 Rev. 3 - Date: 13. March 2007 Document no.:S8-V-3915.01-001 (4) 17247



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